

NGTB50N60FLWG

IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss.

Features

- Low Saturation Voltage using Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5 μ s Short-Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Solar Inverters
- Uninterruptible Power Supplies (UPS)

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------|-------------|------------------|
| Collector-emitter voltage | V_{CES} | 600 | V |
| Collector current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | I_C | 100 50 | A |
| Diode Forward Current @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | I_F | 100 50 | A |
| Diode Pulsed Current T_{PULSE} Limited by $T_{J\text{Max}}$ | I_{FM} | 200 | A |
| Pulsed collector current, T_{pulse} limited by $T_{J\text{max}}$ | I_{CM} | 200 | A |
| Short-circuit withstand time $V_{GE} = 15\text{ V}$, $V_{CE} = 300\text{ V}$, $T_J \leq +150^\circ\text{C}$ | t_{SC} | 5 | μs |
| Gate-emitter voltage | V_{GE} | ± 20 | V |
| Transient gate-emitter voltage ($T_{PULSE} = 5\ \mu\text{s}$, $D < 0.10$) | | ± 30 | V |
| Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$ | P_D | 223 89 | W |
| Operating junction temperature range | T_J | -55 to +150 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| Lead temperature for soldering, 1/8" from case for 5 seconds | T_{SLD} | 260 | $^\circ\text{C}$ |

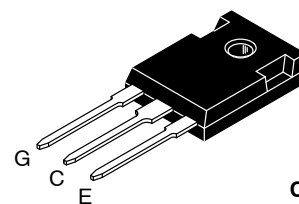
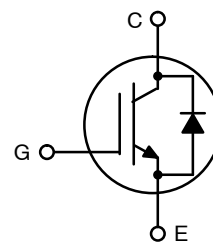
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor[®]

<http://onsemi.com>

50 A, 600 V
 $V_{CEsat} = 1.65\text{ V}$
 $E_{OFF} = 0.6\text{ mJ}$



**TO-247
CASE 340L
STYLE 4**

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|---------------|---------------------|-----------------|
| NGTB50N60FLWG | TO-247 (Pb-Free) | 30 Units / Rail |

NGTB50N60FLWG

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|--|-----------------|-------|-----------------------------|
| Thermal resistance junction-to-case, for IGBT | $R_{\theta JC}$ | 0.56 | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction-to-case, for Diode | $R_{\theta JC}$ | 0.74 | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance junction-to-ambient | $R_{\theta JA}$ | 40 | $^{\circ}\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

STATIC CHARACTERISTIC

| | | | | | | |
|---|---|---------------|-----------|--------------|-----------|----|
| Collector-emitter breakdown voltage, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$ | $V_{(BR)CES}$ | 600 | - | - | V |
| Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 50\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 150^{\circ}\text{C}$ | V_{CEsat} | 1.40 - | 1.65 1.85 | 1.90 - | V |
| Gate-emitter threshold voltage | $V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$ | $V_{GE(th)}$ | 4.5 | 5.5 | 6.5 | V |
| Collector-emitter cut-off current, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 150^{\circ}\text{C}$ | I_{CES} | - - | - - | 0.5 2 | mA |
| Gate leakage current, collector-emitter short-circuited | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | - | - | 200 | nA |

DYNAMIC CHARACTERISTIC

| | | | | | | |
|------------------------------|--|-----------|---|------|---|----|
| Input capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{ies} | - | 7500 | - | pF |
| Output capacitance | | C_{oes} | - | 300 | - | |
| Reverse transfer capacitance | | C_{res} | - | 190 | - | |
| Gate charge total | $V_{CE} = 480\text{ V}, I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ | Q_g | - | 310 | - | nC |
| Gate to emitter charge | | Q_{ge} | - | 60 | - | |
| Gate to collector charge | | Q_{gc} | - | 150 | - | |

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

| | | | | | | | |
|-------------------------|--|--------------|-------|-----|-----|----|----|
| Turn-on delay time | $T_J = 25^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 50\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(on)}$ | - | 116 | - | ns | |
| Rise time | | t_r | - | 43 | - | | |
| Turn-off delay time | | $t_{d(off)}$ | - | 292 | - | | |
| Fall time | | | t_f | - | 78 | - | mJ |
| Turn-on switching loss | | E_{on} | - | 1.1 | - | | |
| Turn-off switching loss | | E_{off} | - | 0.6 | - | | |
| Total switching loss | | E_{ts} | - | 1.7 | - | | |
| Turn-on delay time | $T_J = 150^{\circ}\text{C}$ $V_{CC} = 400\text{ V}, I_C = 50\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(on)}$ | - | 110 | - | ns | |
| Rise time | | t_r | - | 45 | - | | |
| Turn-off delay time | | $t_{d(off)}$ | - | 300 | - | | |
| Fall time | | | t_f | - | 105 | - | mJ |
| Turn-on switching loss | | E_{on} | - | 1.4 | - | | |
| Turn-off switching loss | | E_{off} | - | 1.1 | - | | |
| Total switching loss | | E_{ts} | - | 2.5 | - | | |

DIODE CHARACTERISTIC

| | | | | | | |
|--------------------------|---|-----------|-----------|--------------|----------|---------------|
| Forward voltage | $V_{GE} = 0\text{ V}, I_F = 50\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 50\text{ A}, T_J = 150^{\circ}\text{C}$ | V_F | 1.55 - | 1.85 1.85 | 2.1 - | V |
| Reverse recovery time | $T_J = 25^{\circ}\text{C}$ $I_F = 50\text{ A}, V_R = 200\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ | t_{rr} | - | 85 | - | ns |
| Reverse recovery charge | | Q_{rr} | - | 0.40 | - | μC |
| Reverse recovery current | | I_{rrm} | - | 8 | - | A |

NGTB50N60FLWG

TYPICAL CHARACTERISTICS

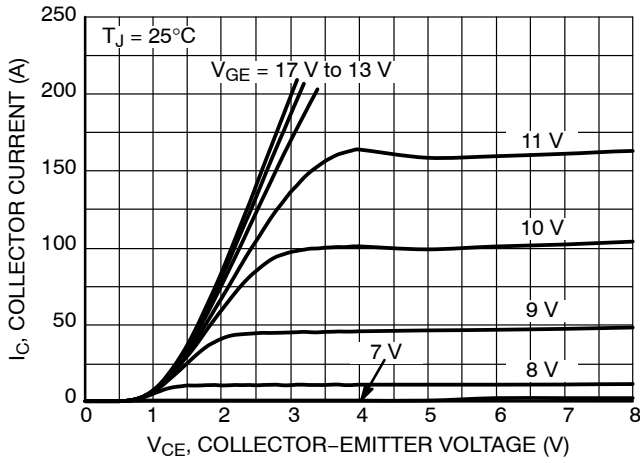


Figure 1. Output Characteristics

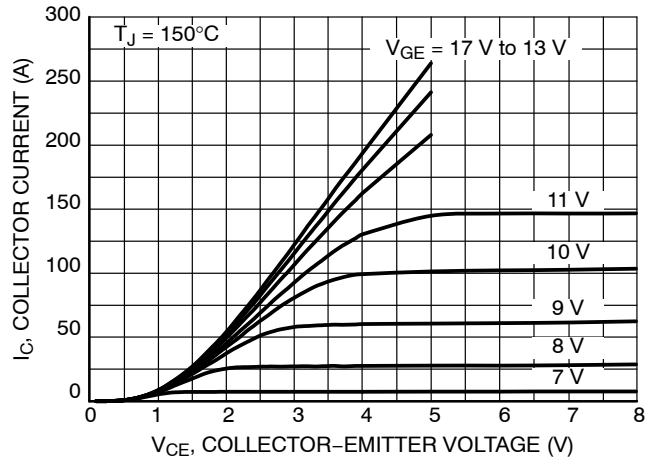


Figure 2. Output Characteristics

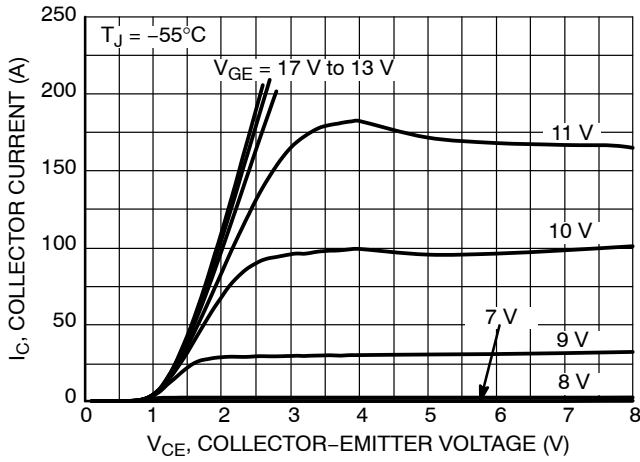


Figure 3. Output Characteristics

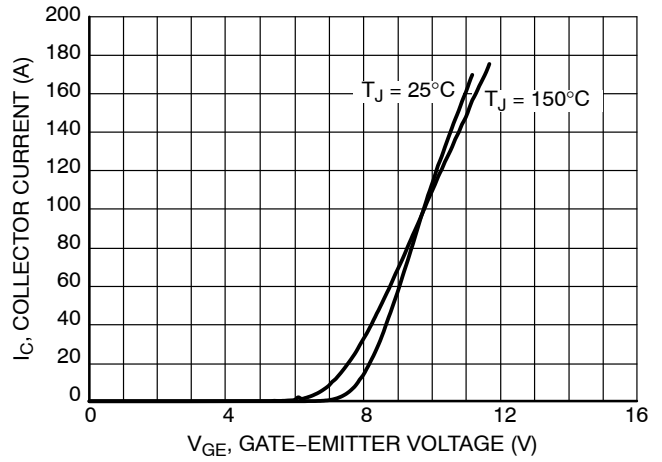


Figure 4. Typical Transfer Characteristics

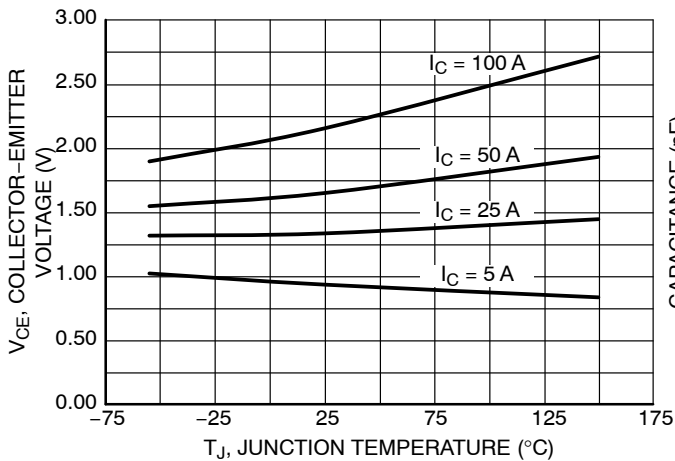


Figure 5. $V_{CE(sat)}$ vs. T_J

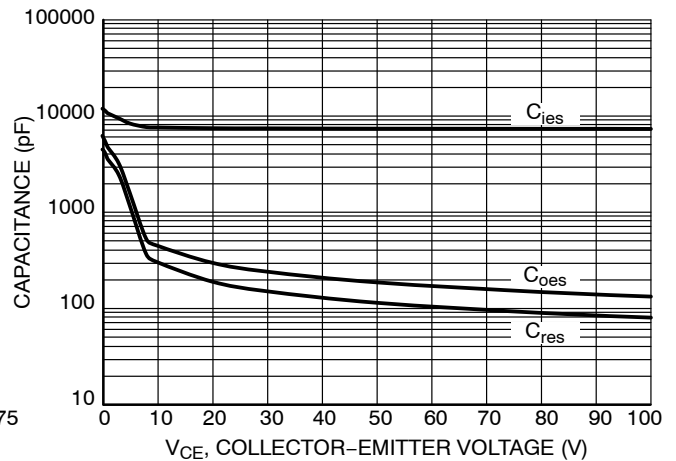


Figure 6. Typical Capacitance

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TYPICAL CHARACTERISTICS

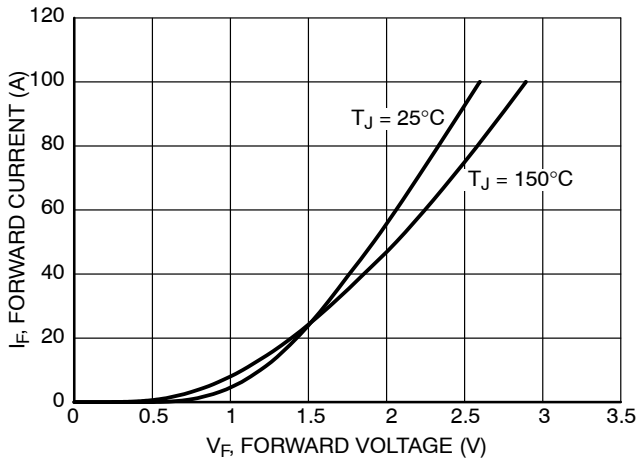


Figure 7. Diode Forward Characteristics

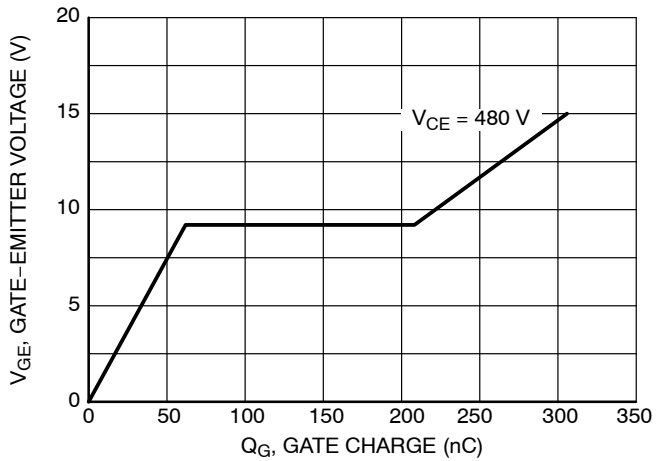


Figure 8. Typical Gate Charge

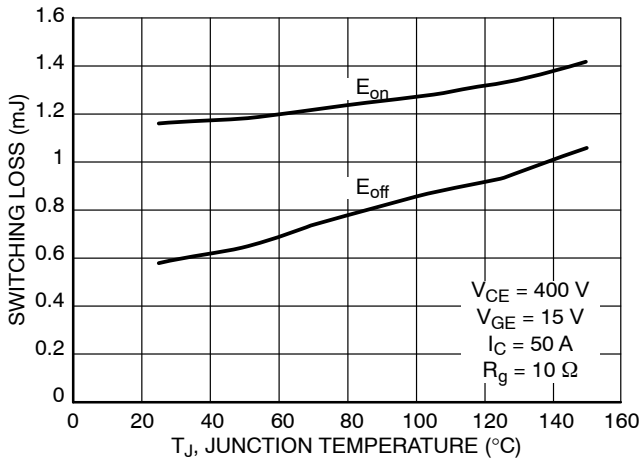


Figure 9. Switching Loss vs. Temperature

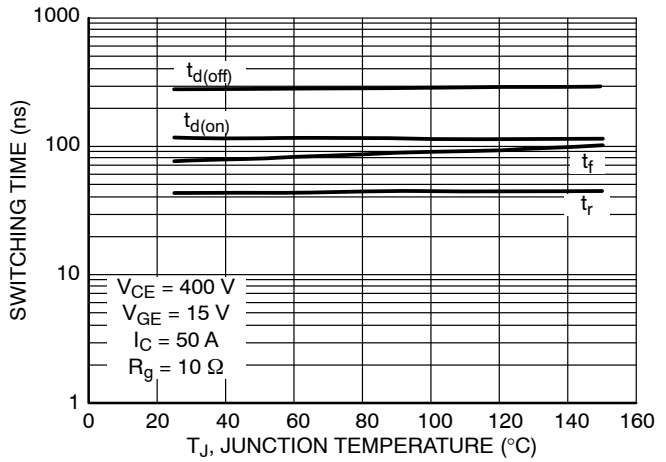


Figure 10. Switching Time vs. Temperature

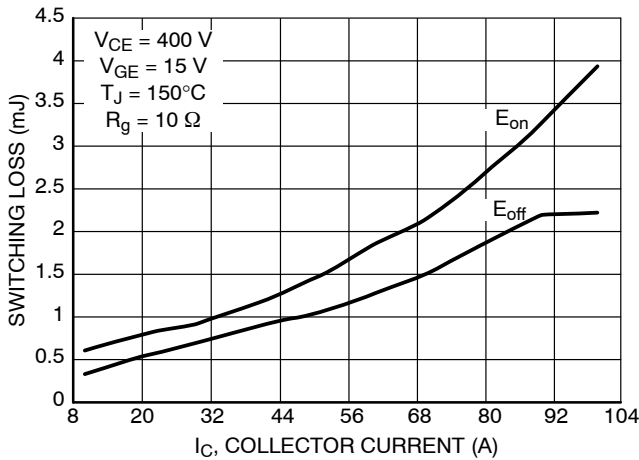


Figure 11. Switching Loss vs. I_C

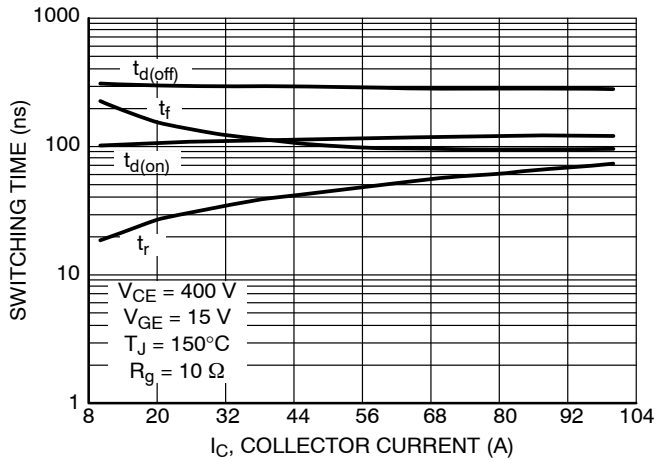


Figure 12. Switching Time vs. I_C

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TYPICAL CHARACTERISTICS

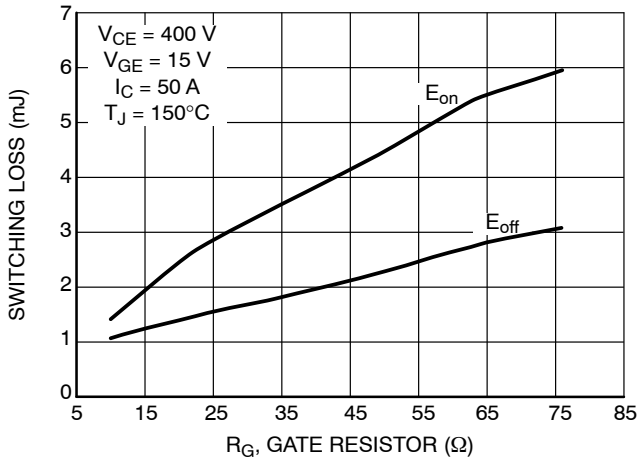


Figure 13. Switching Loss vs. R_G

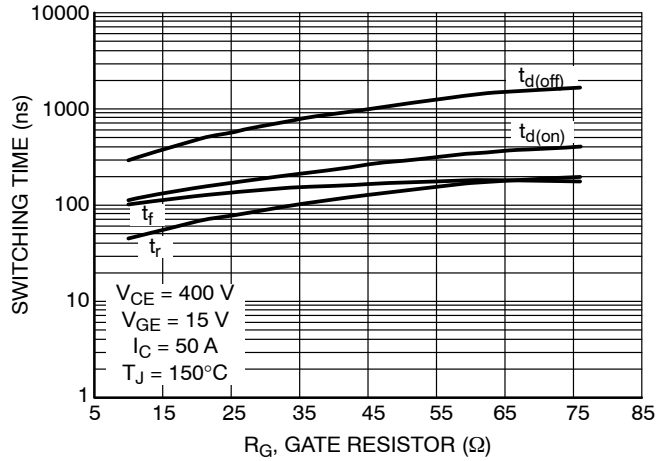


Figure 14. Switching Time vs. R_G

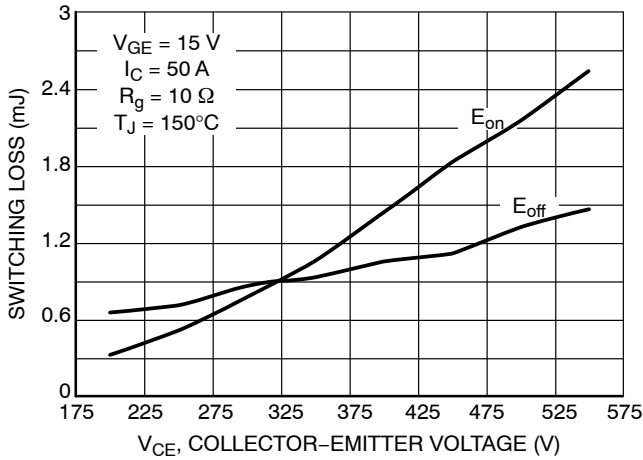


Figure 15. Switching Loss vs. V_{CE}

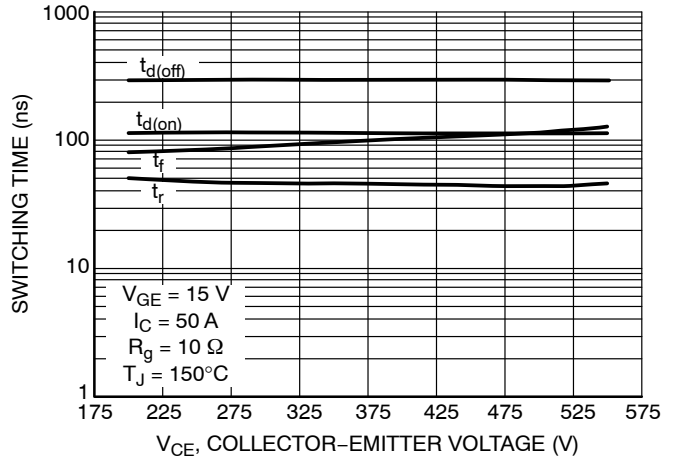


Figure 16. Switching Time vs. V_{CE}

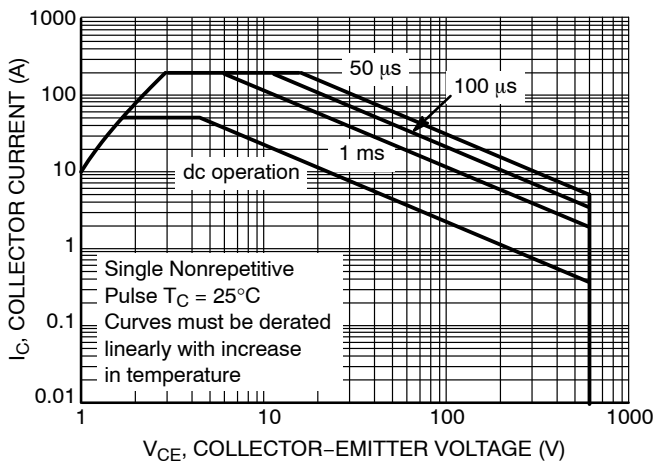


Figure 17. Safe Operating Area

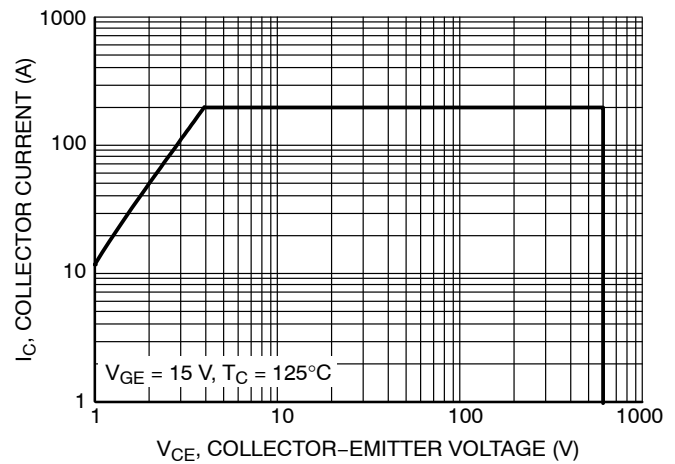


Figure 18. Reverse Bias Safe Operating Area

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TYPICAL CHARACTERISTICS

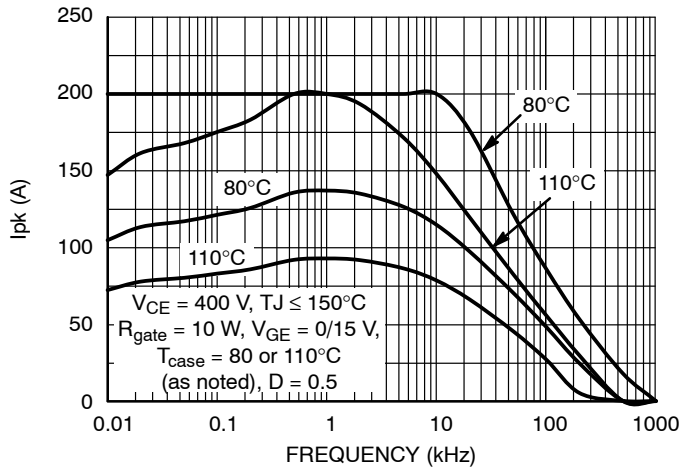


Figure 19. Collector Current vs. Switching Frequency

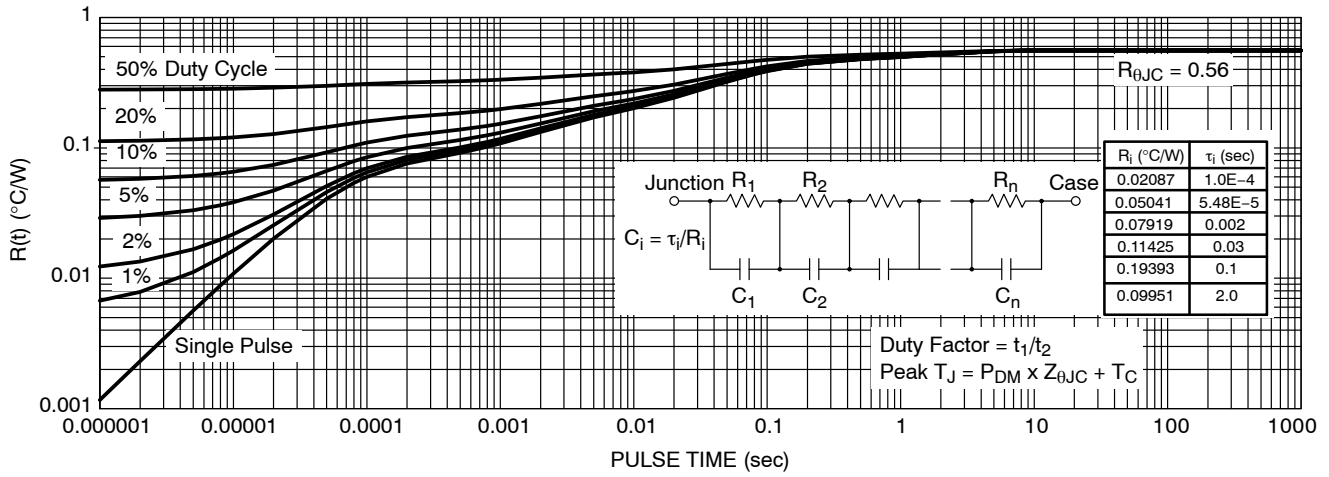


Figure 20. IGBT Transient Thermal Impedance

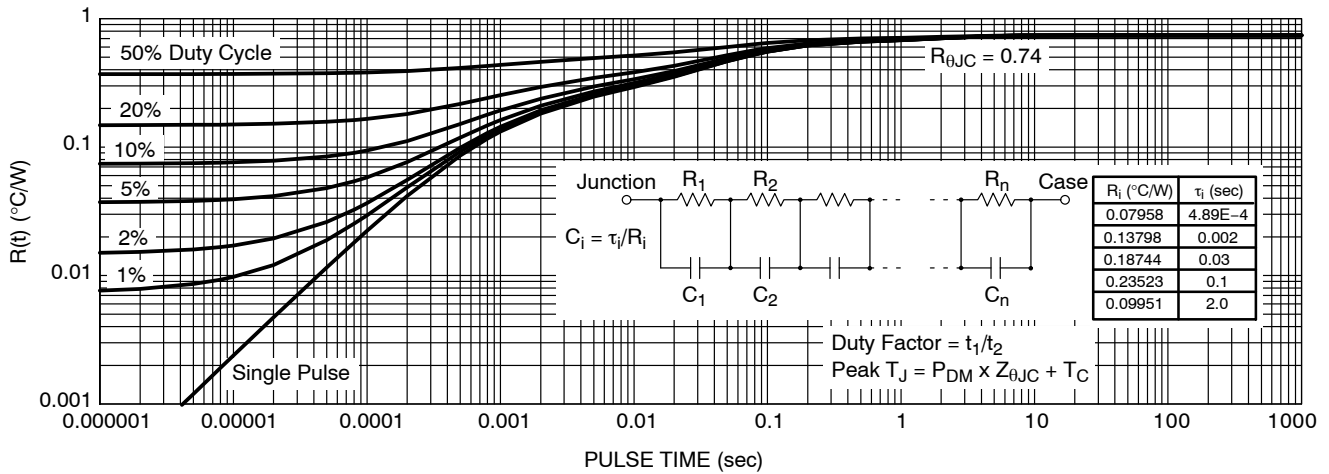


Figure 21. Diode Transient Thermal Impedance

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Figure 22. Test Circuit for Switching Characteristics

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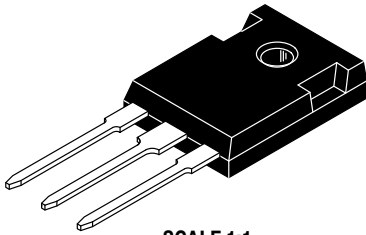


Figure 23. Definition of Turn On Waveform



Figure 24. Definition of Turn Off Waveform

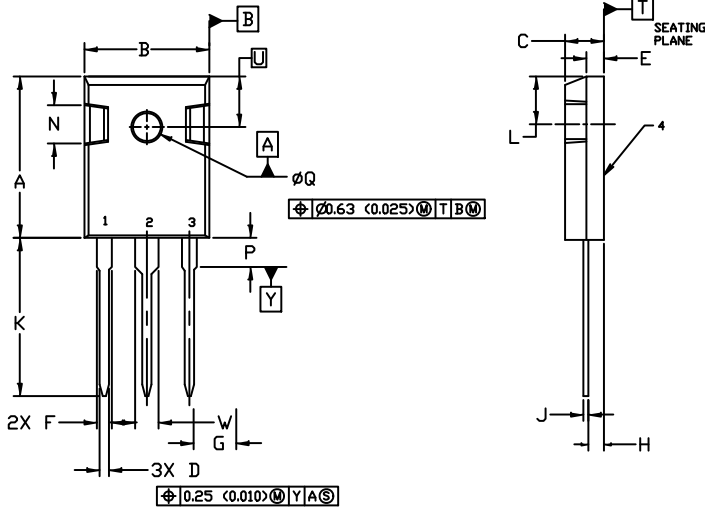
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



TO-247
CASE 340L
ISSUE G

DATE 06 OCT 2021

SCALE 1:1

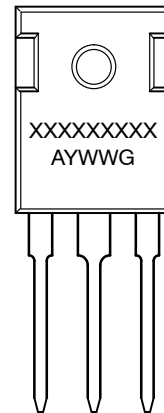


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 20.32 | 21.08 | 0.800 | 0.830 |
| B | 15.75 | 16.26 | 0.620 | 0.640 |
| C | 4.70 | 5.30 | 0.185 | 0.209 |
| D | 1.00 | 1.40 | 0.040 | 0.055 |
| E | 1.90 | 2.60 | 0.075 | 0.102 |
| F | 1.65 | 2.13 | 0.065 | 0.084 |
| G | 5.45 BSC | | 0.215 BSC | |
| H | 1.50 | 2.49 | 0.059 | 0.098 |
| J | 0.40 | 0.80 | 0.016 | 0.031 |
| K | 19.81 | 20.83 | 0.780 | 0.820 |
| L | 5.40 | 6.20 | 0.212 | 0.244 |
| N | 4.32 | 5.49 | 0.170 | 0.216 |
| P | ---- | 4.50 | ---- | 0.177 |
| Q | 3.55 | 3.65 | 0.140 | 0.144 |
| U | 6.15 BSC | | 0.242 BSC | |
| W | 2.87 | 3.12 | 0.113 | 0.123 |

GENERIC
MARKING DIAGRAM*



- | | | | |
|--|--|--|--|
| <p>STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN</p> | <p>STYLE 2: PIN 1. ANODE 2. CATHODE (S) 3. ANODE 2 4. CATHODES (S)</p> | <p>STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR</p> | <p>STYLE 4: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR</p> |
| <p>STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE</p> | <p>STYLE 6: PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2 3. GATE 4. MAIN TERMINAL 2</p> | | |

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|------------------|-------------|--|
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| DESCRIPTION: | TO-247 | PAGE 1 OF 1 |

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